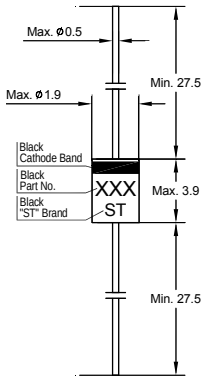
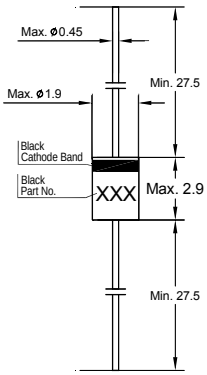
1N4149...1N4454

SILICON EPITAXIAL PLANAR DIODES

for general purpose and switching



Glass Case DO-35
Dimensions in mm



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings and Characteristics (T_a = 25 °C unless otherwise specified.)

Type	Peak Reverse Voltage	Max. Average Rectified Current	Max. Power Dissipation at 25 °C	Max. Junction Temp.	Max. Forward Voltage		Max. Reverse Current		Max. Reverse Recovery Time	
	V_{RM} (V)	I_O (mA) [2]	P_{tot} (mW) [2]	T_j (°C)	V_F (V)	at I_F (mA)	I_R (nA)	at V_R (V)	t_{rr} (ns)	Conditions
1N4149 [1]	100	150	500	200	1	10	25	20	4	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, to I_R = 1 mA
1N4151	75	150	500	200	1	50	50	50	2	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, to I_R = 1 mA
1N4152	40	150	400	175	0.55	0.1	50	30	2	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, to I_R = 1 mA
1N4154	35	150	500	200	1	30	100	25	2	I_F = 10 mA, V_R = 6V, R_L = 100 Ω, to I_R = 1 mA
1N4447 [1]	100	150	500	200	1	20	25	20	4	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, to I_R = 1 mA
1N4449 [1]	100	150	500	200	1	30	25	20	4	I_F = 10 mA, V_R = 6 V, R_L = 100 Ω, to I_R = 1 mA
1N4450	40	150	400	175	0.54	0.5	50	30	4	I_F = I_R = 10 mA , to I_R = 1 mA
1N4451	40	150	400	175	0.5	0.1	50	30	10	I_F = I_R = 10 mA , to I_R = 1 mA
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1	10	100	50	4	I_F = I_R = 10 mA , to I_R = 1 mA

[1] These diodes are also available in glass case DO-34. Parameter for diodes in case DO-34: P_{tot} = 300 mW, T_j = 175 °C
[2] Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.